

2N3905  
2N3906

PNP SILICON TRANSISTOR



TO-92 CASE



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR 2N3905 and 2N3906 types are PNP silicon transistors designed for general purpose amplifier and switching applications. NPN complementary types are 2N3903 and 2N3904.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: ( $T_A=25^{\circ}\text{C}$ )

Collector-Base Voltage  
Collector-Emitter Voltage  
Emitter-Base Voltage  
Continuous Collector Current  
Power Dissipation  
Operating and Storage Junction Temperature  
Thermal Resistance

SYMBOL

$V_{CBO}$  40  
 $V_{CEO}$  40  
 $V_{EBO}$  5.0  
 $I_C$  200  
 $P_D$  625  
 $T_J, T_{stg}$  -65 to +150  
 $\Theta_{JA}$  200

UNITS

V  
V  
V  
mA  
mW  
 $^{\circ}\text{C}$   
 $^{\circ}\text{C/W}$

ELECTRICAL CHARACTERISTICS: ( $T_A=25^{\circ}\text{C}$ )

SYMBOL	TEST CONDITIONS	2N3905		2N3906		UNITS
		MIN	MAX	MIN	MAX	
$I_{CEV}$	$V_{CE}=30\text{V}, V_{EB}=3.0\text{V}$	-	50	-	50	nA
$BV_{CBO}$	$I_C=10\mu\text{A}$	40	-	40	-	V
$BV_{CEO}$	$I_C=1.0\text{mA}$	40	-	40	-	V
$BV_{EBO}$	$I_E=10\mu\text{A}$	5.0	-	5.0	-	V
$V_{CE(SAT)}$	$I_C=10\text{mA}, I_B=1.0\text{mA}$	-	0.25	-	0.25	V
$V_{CE(SAT)}$	$I_C=50\text{mA}, I_B=5.0\text{mA}$	-	0.4	-	0.4	V
$V_{BE(SAT)}$	$I_C=10\text{mA}, I_B=1.0\text{mA}$	0.65	0.85	0.65	0.85	V
$V_{BE(SAT)}$	$I_C=50\text{mA}, I_B=5.0\text{mA}$	-	0.95	-	0.95	V
$h_{FE}$	$V_{CE}=1.0\text{V}, I_C=0.1\text{mA}$	30	-	60	-	
$h_{FE}$	$V_{CE}=1.0\text{V}, I_C=1.0\text{mA}$	40	-	80	-	
$h_{FE}$	$V_{CE}=1.0\text{V}, I_C=10\text{mA}$	50	150	100	300	
$h_{FE}$	$V_{CE}=1.0\text{V}, I_C=50\text{mA}$	30	-	60	-	
$h_{FE}$	$V_{CE}=1.0\text{V}, I_C=100\text{mA}$	15	-	30	-	
$h_{fe}$	$V_{CE}=10\text{V}, I_C=1.0\text{mA}, f=1.0\text{kHz}$	50	200	100	400	
$f_T$	$V_{CE}=20\text{V}, I_C=10\text{mA}, f=100\text{MHz}$	200	-	250	-	MHz
$C_{ob}$	$V_{CB}=5.0\text{V}, I_E=0, f=100\text{kHz}$	-	4.5	-	4.5	pF
$C_{ib}$	$V_{EB}=0.5\text{V}, I_C=0, f=100\text{kHz}$	-	10	-	10	pF
NF	$V_{CE}=5.0\text{V}, I_C=100\mu\text{A}, R_S=1.0\text{k}\Omega$ $f=10\text{Hz to } 15.7\text{kHz}$	-	5.0	-	4.0	dB
$t_{on}$	$V_{CC}=3.0\text{V}, V_{BE(OFF)}=0.5\text{V}, I_C=10\text{mA}$ $I_{B1}=1.0\text{mA}$	-	70	-	70	ns
$t_{off}$	$V_{CC}=3.0\text{V}, I_C=10\text{mA}, I_{B1}=I_{B2}=1.0\text{mA}$	-	260	-	300	ns

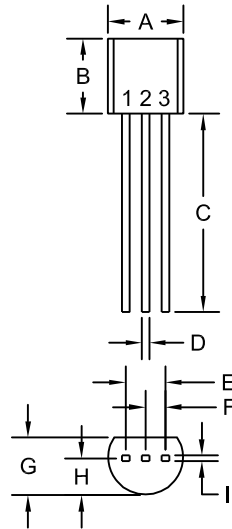
R2 (17-October 2011)

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### TO-92 CASE - MECHANICAL OUTLINE



DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A (DIA)	0.175	0.205	4.45	5.21
B	0.170	0.210	4.32	5.33
C	0.500	-	12.70	-
D	0.016	0.022	0.41	0.56
E	0.100		2.54	
F	0.050		1.27	
G	0.125	0.165	3.18	4.19
H	0.080	0.105	2.03	2.67
I	0.015		0.38	

TO-92 (REV: R1)

#### LEAD CODE:

- 1) Emitter
- 2) Base
- 3) Collector

**MARKING:**  
**FULL PART NUMBER**

R2 (17-October 2011)